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| --- |
| Objective |
| Batch name:  |
| This is an example process flow to be used as a template. It should contain* The objective of the process.
* Substrates/samples used in the flow. Both actual samples to be processed (device wafers) and monitor samples for the different process steps
* The Process flow main processes and steps
* Recommended: Figures illustrating the sample before and after each main process step.

How to use this template (works only with the .dotx template file):* Fill out the fields in the heading!
* Add process steps in the following way:
	1. Select a process step header and one or more detail steps. Make sure to select the whole line so that the marking extends beyond the table to the right.
	2. Press <crtl> C to copy the part.
	3. Select the step header where you want to insert the new step. Again make sure to select the whole line.
	4. Press <ctrl> V to insert to new step.
* The Content (TOC) on the last page is an option, but can give a nice overview for very long process flows.
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| Substrates |
| Substrate | Orient. | Size | Doping/type | Polish | thickness | Box | Purpose | # | Sample ID |
| Silicon  | <100> | 4” | n (Phos.) | SSP | 525±25µm |  | Device wafers | 2 | S1-S2 |
| Silicon  | <100> | 4” | n (Phos.) | SSP | 525±25µm |  | Test wafers | 1 | T1 |

Comments: Number of wafers is for illustration only

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| --- |
| Figures |
| Figure | Caption | Step | Figure |
|  | After SiO2 dep | 2.1 |  |
|  | After lithography | 3.5 |  |
|  | After BHF etch | 4.1 |  |
|  | After resist strip | 4.4 |  |
|  | After lithography | 5.8 |  |
|  | After metal deposition | 6.1 |  |
|  | After lift-off | 6.2 |  |

Comments:Click here to enter text.

|  |  |  |  |
| --- | --- | --- | --- |
| Step Heading | Equipment | Procedure | Comments |
| 1. Preparation
 | **All wafers** |
| * 1. Wafer selection
 | Wafer box | Take the wafers from the storage and put them in a wafer box.  | Note the wafer IDs in the batch traveler |
| 1. SiO2 deposition
 | **All wafers** |
| * 1. SiO2 dry oxidation
 | Phosphor Drive-in (A3) | Place a test wafer in the center of the boat and place device wafers and eg. test wafers equally distributed on each side of the test wafer. No spacing between wafers.Recipe: Dry1050, time:100minTarget thickness: 100±10nm | Measure oxide thickness on the filmtech and note the result in the furnace log |
| 1. Lithography – 1.5µm standard
 | **All wafers** |
| * 1. Surface treatment
 | HMDS oven | Load all wafers in oven for ~30 minsRecipe: program 4 | Note time in logbook |
| * 1. Clean spinner
 | SSE spinner | Clean spinner nozzle and run the dummy wafersRecipe: 1.5 4inch | 1-3 dummiesNote time in logbook |
| * 1. Coat wafers
 | SSE spinner | Coat the device wafers1.5 m AZ5214e Novolac resistSoftbake on hotplate Recipe: 1.5 4inch (Temp: 90°C, time:60 sec) | Resist thickness not checkedNote time in logbook |
| * 1. Exposure
 | Aligner-6inch | Align to flat. Hard contactRecipe: xxxxxxExposure time: 3 secMask: CONTACTS (dark field) | Note time in logbook |
| * 1. Develop
 | Developer bench | Develop in 351B for 60±10 sec | Note time in logbook |
| * 1. Rinse/dry
 | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| * 1. Inspection
 | Optical microscope | Check pattern and alignment marks |  |
| 1. SiO2 etch
 | **All wafers** |
| * 1. BHF etch
 | Buffered HF Clean | Etching rate: 75-80 nm/minTime: 90 sec |  |
| * 1. Rinse/dry
 | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| * 1. Inspection
 | Optical microscope | Check pattern and alignment |  |
| * 1. Strip resist
 | Acetone | First 2-3 min in rough followed by 5 min in fine strip bath with US |  |
| * 1. Rinse/dry
 | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| * 1. Inspection
 | Dektak | Measure step heightTarget: 100±10 nm |  |
| 1. Lithography – 2.2µm image reversal
 | **All wafers** |
| * 1. Surface treatment
 | HMDS oven | Load all wafers in oven for ~30 minsRecipe: program 4 | Note time in logbook |
| * 1. Clean spinner
 | SSE spinner | Clean spinner nozzle and run the dummy wafersRecipe: 2.2 4inch | 1-3 dummiesNote time in logbook |
| * 1. AZ5214 resist coating
 | SSE spinner | Coat the device wafers2.2 m AZ5214e Novolac resistRecipe: 2.2 4inch (Temp: 90°C, time:60 sec) | Resist thickness not checkedNote time in logbook |
| * 1. Exposure
 | Aligner-6inch | Align to alignment marks on wafer. Hard contact.Recipe: XXXXXExposure time: 1.7 secMask: METAL (clear field) | Note time in logbook |
| * 1. Reverse bake
 | SSE spinner | Temp: 110 °CTime: 120 sec |  |
| * 1. Flood exposure
 | Aligner-6inch | Recipe: XXXXXExposure time: 15 secMask: none | Note time in logbook |
| * 1. Transport of wafers
 | transport box | Load wafers into the Black or blue transport box | To avoid unwanted exposure from the white light |
| * 1. Develop
 | Developerbench | Develop in 70±10 sec | Note time in logbook |
| * 1. Rinse/dry
 | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| * 1. Inspection
 | Optical microscope | Alignment check |  |
| 1. Aluminum pattern
 | **Only device wafers!!** |
| * 1. Aluminum deposition
 | Alcatel | Metal: AlThickness: 200 nm  | Note time in logbook |
| * 1. Lift-off
 | Lift-off bench | Leave wafers in acetone for 2-3 min. Start the US for 10 min. Rotate wafers and start US for another 10 min. | Fill the bench with Acetone until carrier is covered. |
| * 1. Rinse/dry
 | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| * 1. Inspection
 | Optical microscope | Check for completeness |  |
| * 1. Inspection
 | Dektak | Measure heights and widths | Note on measurement sheet |
| 1. Linewidth measurement
 | **All wafers** |
| * 1. Optical inspection
 | Nikon ECLIPSE L200 | Measure linewidths | Note on measurement sheet |
| * 1. Electrical characterization
 | Probe station | Measure sheet resistance and line resistance and calculate linewidth from this | Note on measurement sheet |
| * 1. SEM inspection
 | SEM-Zeiss/Leo | Measure linewidths | Note on measurement sheet |

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